

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend the paragraph starting at page 5, line 8 as follows:

~~Light-emitting~~ A light-emitting device with excellent emission characteristics is produced by fabricating the light-emitting device using the epitaxial substrate produced in the foregoing manner.

Please amend the paragraph starting at page 18, line 12 as follows:

Next, the surface was formed with a pattern for a p-type electrode by photolithography, Ni and Au were deposited by vacuum vapor deposition, an electrode pattern was formed by liftoff, and the result was heat treated to form the ohmic *p* electrode 13. A mask pattern was then formed by photolithography and dry etching was conducted to expose the *n* layer. After mask removal, a pattern for an *n* electrode was formed on the dry-etched surface by photolithography, Al was deposited by vacuum vapor deposition, and an electrode pattern was formed by liftoff to serve as the *n* electrode 12. The electrode area of the ~~p electrode~~ electrode 13 was $3.14 \times 10^{-4} \text{ cm}^2$.